Hongxing Jiang

List of Publications by Year in descending order

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418	17,995	14124	22488
papers	citations	69 h-index	117 g-index

426	426	426	14131
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Formation energy and optical excitation mechanisms of Er in GaN semi-bulk crystals. Applied Physics Letters, 2022, 120, 052103.	1.5	0
2	Effects of unique band structure of h-BN probed by photocurrent excitation spectroscopy. Applied Physics Express, 2022, 15, 051005.	1.1	4
3	Boron nitride neutron detector with the ability for detecting both thermal and fast neutrons. Applied Physics Letters, 2022, 120, .	1.5	8
4	Electrical transport properties of hexagonal boron nitride epilayers. Semiconductors and Semimetals, 2021, 107, 393-454.	0.4	5
5	Charge collection in h-BN neutron detectors at elevated temperatures. Applied Physics Letters, 2021, 118, 092102.	1.5	7
6	Band structure and ultraviolet optical transitions in ErN. Applied Physics Letters, 2021, 118, .	1.5	2
7	Development of nitride microLEDs and displays. Semiconductors and Semimetals, 2021, , 1-56.	0.4	2
8	Charge collection and trapping mechanisms in hexagonal boron nitride epilayers. Applied Physics Letters, 2021, 119, .	1.5	1
9	Direct detection of rare earth ion distributions in gallium nitride and its influence on growth morphology. Journal of Applied Physics, 2020, 127, 013102.	1.1	6
10	Polarization-resolved Er emission in Er doped GaN bulk crystals. Journal of Applied Physics, 2020, 127, 243107.	1.1	2
11	High efficiency hexagonal boron nitride neutron detectors with 1â€‰cm2 detection areas. Applied Physics Letters, 2020, 116, .	1.5	27
12	Development of microLED. Applied Physics Letters, 2020, 116, .	1.5	152
13	Anisotropic index of refraction and structural properties of hexagonal boron nitride epilayers probed by spectroscopic ellipsometry. Journal of Applied Physics, 2020, 127, .	1.1	10
14	Band structure and infrared optical transitions in ErN. Applied Physics Letters, 2020, 116, 171104.	1.5	5
15	Probing the surface oxidation process in hexagonal boron nitride epilayers. AIP Advances, 2020, 10, 025213.	0.6	7
16	Erbium energy levels in GaN grown by hydride vapor phase epitaxy. AIP Advances, 2020, 10, .	0.6	2
17	Lateral charge carrier transport properties of B-10 enriched hexagonal BN thick epilayers. Applied Physics Letters, 2019, 115, 072108.	1.5	16
18	Optical properties of GaN/Er:GaN/GaN coreâ€“cladding planar waveguides. Applied Physics Express, 2019, 12, 075505.	1.1	7

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19	Critical thickness of hexagonal GaBN/BN heterostructures. Journal of Applied Physics, 2019, 125, .	1.1	5
20	Growth and fabrication of GaN/Er:GaN/GaN core-cladding planar waveguides. Applied Physics Letters, 2019, 114, 222105.	1.5	10
21	High sensitivity hexagonal boron nitride lateral neutron detectors. Applied Physics Letters, 2019, 114, .	1.5	21
22	Effects of surface recombination on the charge collection in h-BN neutron detectors. Journal of Applied Physics, 2019, 125, 104501.	1.1	13
23	Development of Micro-LEDs and Applications. , 2019, , .		0
24	Synthesis and photoluminescence properties of hexagonal BGaN alloys and quantum wells. Applied Physics Express, 2019, 12, 011002.	1.1	4
25	Room-Temperature Lasing Action in GaN Quantum Wells in the Infrared 1.5 Î¼m Region. ACS Photonics, 2018, 5, 1303-1309.	3.2	16
26	Origin and roles of oxygen impurities in hexagonal boron nitride epilayers. Applied Physics Letters, 2018, 112, .	1.5	37
27	Hexagonal boron nitride neutron detectors with high detection efficiencies. Journal of Applied Physics, 2018, 123, .	1.1	40
28	Resonant excitation cross-sections of erbium in freestanding GaN bulk crystals. Applied Physics Letters, 2018, 112, .	1.5	5
29	Erbium-doped GaN bulk crystals as a gain medium for eye-safe high energy lasers. , 2018, , .		1
30	Telecommunication-Wavelength Lasing in Er-doped GaN Multiple Quantum Wells at Room Temperature. , 2018, , .		0
31	Photoluminescence quantum efficiency of Er optical centers in GaN epilayers. Scientific Reports, 2017, 7, 39997.	1.6	9
32	Hyperspectral Nonlinear Optical Light Generation from a Monolithic GaN Microcavity. Advanced Optical Materials, 2017, 5, 1600804.	3.6	8
33	Probing carbon impurities in hexagonal boron nitride epilayers. Applied Physics Letters, 2017, 110, .	1.5	36
34	Layer number dependent optical properties of multilayer hexagonal BN epilayers. Applied Physics Letters, 2017, 110, .	1.5	24
35	Response of alpha particles in hexagonal boron nitride neutron detectors. Applied Physics Letters, 2017, 110, .	1.5	2
36	Excitation and emission mechanisms of Er:GaN gain medium in 1.5â€‰Î¼m region. Applied Physics Letters, 2017, 111, .	1.5	7

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37	Temperature dependence studies of Er optical centers in GaN epilayers grown by MOCVD. MRS Advances, 2017, 2, 135-140.	0.5	2
38	Annealing of dry etch damage in metallized and bare (-201) Ga2O3. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	48
39	Toward achieving flexible and high sensitivity hexagonal boron nitride neutron detectors. Applied Physics Letters, 2017, 111, .	1.5	31
40	Large-Scale Growth of High-Quality Hexagonal Boron Nitride Crystals at Atmospheric Pressure from an Feâ€“Cr Flux. Crystal Growth and Design, 2017, 17, 4932-4935.	1.4	49
41	Reviewâ€”Hexagonal Boron Nitride Epilayers: Growth, Optical Properties and Device Applications. ECS Journal of Solid State Science and Technology, 2017, 6, Q3012-Q3021.	0.9	64
42	Hexagonal boron nitride epilayers for deep UV photonics. , 2017, , .		0
43	Temperature dependence of the energy bandgap of multi-layer hexagonal boron nitride. Applied Physics Letters, 2017, 111, 132106.	1.5	10
44	High-efficiency and high-sensitivity thermal neutron detectors based on hexagonal BN epilayers. , 2017, , .		2
45	Rare Earth doped GaN for photonic devices. , 2017, , .		0
46	Current injection 154 Âµm light-emitting devices based on Er-doped GaN/AlGaN multiple quantum wells. Optical Materials Express, 2016, 6, 3476.	1.6	4
47	Toward the realization of erbium-doped GaN bulk crystals as a gain medium for high energy lasers. Applied Physics Letters, 2016, 109, .	1.5	14
48	Growth and device processing of hexagonal boron nitride epilayers for thermal neutron and deep ultraviolet detectors. AIP Advances, 2016, 6, .	0.6	25
49	Realization of highly efficient hexagonal boron nitride neutron detectors. Applied Physics Letters, 2016, 109, .	1.5	75
50	The origins of near band-edge transitions in hexagonal boron nitride epilayers. Applied Physics Letters, 2016, 108, .	1.5	46
51	Bandgap and exciton binding energies of hexagonal boron nitride probed by photocurrent excitation spectroscopy. Applied Physics Letters, 2016, 109, .	1.5	43
52	Nature of exciton transitions in hexagonal boron nitride. Applied Physics Letters, 2016, 108, .	1.5	18
53	Thermal neutron detectors based on hexagonal boron nitride epilayers. , 2016, , .		3
54	Enhancement of 1.5â€‰Î¼m emission under 980â€‰nm resonant excitation in Er and Yb co-doped GaN epilayers. Applied Physics Letters, 2016, 109, .	1.5	8

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55	Optical excitation of Er centers in GaN epilayers grown by MOCVD. , 2016, , .		0
56	Optical and electrical properties of Mg-doped AlN nanowires grown by molecular beam epitaxy. Applied Physics Letters, 2015, 106, .	1.5	50
57	Excitation mechanisms of Er optical centers in GaN epilayers. Applied Physics Letters, 2015, 107, 171105.	1.5	23
58	p-Type AlN nanowires and AlN nanowire light emitting diodes on Si. , 2015, , .		0
59	Hexagonal boron nitride thin film thermal neutron detectors with high energy resolution of the reaction products. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2015, 783, 121-127.	0.7	49
60	Erbium-doped a-plane GaN epilayers synthesized by metal-organic chemical vapor deposition. Optical Materials Express, 2015, 5, 274.	1.6	3
61	A Simplified Method of Making Flexible Blue LEDs on a Plastic Substrate. IEEE Photonics Journal, 2015, 7, 1-7.	1.0	35
62	Erbium doped GaN synthesized by hydride vapor-phase epitaxy. Optical Materials Express, 2015, 5, 596.	1.6	7
63	Erbium-doped AlN epilayers synthesized by metal-organic chemical vapor deposition. Optical Materials Express, 2015, 5, 648.	1.6	3
64	The origin of deep-level impurity transitions in hexagonal boron nitride. Applied Physics Letters, 2015, 106, .	1.5	76
65	Dramatic enhancement of 1.54â€‰Î¼m emission in Er doped GaN quantum well structures. Applied Physics Letters, 2015, 106, 121106.	1.5	13
66	Carbon-rich hexagonal (BN)C alloys. Journal of Applied Physics, 2015, 117, .	1.1	20
67	Hexagonal boron nitride for deep UV photonics. , 2015, , .		0
68	Hexagonal boron nitride for deep ultraviolet photonic devices. Semiconductor Science and Technology, 2014, 29, 084003.	1.0	121
69	Refractive index of erbium doped GaN thin films. Applied Physics Letters, 2014, 105, 081104.	1.5	9
70	Charge carrier transport properties in layer structured hexagonal boron nitride. AIP Advances, 2014, 4, .	0.6	28
71	Layer-structured hexagonal (BN)C semiconductor alloys with tunable optical and electrical properties. Journal of Applied Physics, 2014, 115, .	1.1	38
72	Excitation cross section of erbium-doped GaN waveguides under 980â€‰nm optical pumping. Applied Physics Letters, 2014, 105, 051106.	1.5	6

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73	Effects of Mg-doped AlN/AlGaN superlattices on properties of p-GaN contact layer and performance of deep ultraviolet light emitting diodes. AIP Advances, 2014, 4, 047122.	0.6	20
74	Electrical transport properties of (BN)-rich hexagonal (BN)C semiconductor alloys. AIP Advances, 2014, 4, 087141.	0.6	21
75	Optical properties of strain-free AlN nanowires grown by molecular beam epitaxy on Si substrates. Applied Physics Letters, 2014, 104, .	1.5	44
76	Probing of local alloy disorder in InGaN using Er3+ ions. Optical Materials, 2014, 36, 1730-1733.	1.7	4
77	Temperature dependence of the energy bandgap of two-dimensional hexagonal boron nitride probed by excitonic photoluminescence. Journal of Applied Physics, 2014, 115, 053503.	1.1	14
78	Fabrication and characterization of solid-state thermal neutron detectors based on hexagonal boron nitride epilayers. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2014, 748, 84-90.	0.7	51
79	Deep Ultraviolet to Near-Infrared Emission and Photoresponse in Layered N-Doped Graphene Quantum Dots. ACS Nano, 2014, 8, 6312-6320.	7.3	455
80	Realizing InGaN monolithic solar-photoelectrochemical cells for artificial photosynthesis. Applied Physics Letters, 2014, 104, .	1.5	29
81	Crystal field analysis of rare-earth ions energy levels in GaN. Optical Materials, 2014, 37, 165-174.	1.7	20
82	Characterization of bulk hexagonal boron nitride single crystals grown by the metal flux technique. Journal of Crystal Growth, 2014, 403, 110-113.	0.7	33
83	Optoelectronic properties of hexagonal boron nitride epilayers. Proceedings of SPIE, 2013, , .	0.8	4
84	Hexagonal boron nitride and 6H-SiC heterostructures. Applied Physics Letters, 2013, 102, .	1.5	43
85	SiO2/TiO2 distributed Bragg reflector near 1.5 Î¼m fabricated by e-beam evaporation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	0.9	17
86	Effects of double layer AlN buffer layers on properties of Si-doped AlxGa1â^'xN for improved performance of deep ultraviolet light emitting diodes. Journal of Applied Physics, 2013, 113, 123501.	1.1	20
87	Electrical transport properties of Si-doped hexagonal boron nitride epilayers. AIP Advances, 2013, 3, .	0.6	41
88	Optical excitation cross section of erbium in GaN. Applied Optics, 2013, 52, 1132.	0.9	12
89	Correlation between the optical loss and crystalline quality in erbium-doped GaN optical waveguides. Applied Optics, 2013, 52, 5426.	0.9	16
90	Nitride micro-LEDs and beyond - a decade progress review. Optics Express, 2013, 21, A475.	1.7	173

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91	Two-dimensional excitons in three-dimensional hexagonal boron nitride. Applied Physics Letters, 2013, 103, .	1.5	72
92	Suppression of thermal conductivity in InxGa1â^'xN alloys by nanometer-scale disorder. Applied Physics Letters, 2013, 102, 121906.	1.5	53
93	Dry etching techniques for active devices based on hexagonal boron nitride epilayers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, 061517.	0.9	25
94	Metal-semiconductor-metal neutron detectors based on hexagonal boron nitride epitaxial layers. Proceedings of SPIE, 2012, , .	0.8	5
95	Surfactant effects of gallium on quality of AlN epilayers grown via metal-organic chemical-vapour deposition on SiC substrates. Journal Physics D: Applied Physics, 2012, 45, 285103.	1.3	12
96	Nature of optical transitions involving cation vacancies and complexes in AlN and AlGaN. Applied Physics Letters, 2012, 100, .	1.5	46
97	Full-scale self-emissive blue and green microdisplays based on GaN micro-LED arrays. Proceedings of SPIE, 2012, , .	0.8	27
98	Effects of growth pressure on erbium doped GaN infrared emitters synthesized by metal organic chemical vapor deposition. Optical Materials Express, 2012, 2, 1095.	1.6	9
99	High quality AlN grown on double layer AlN buffers on SiC substrate for deep ultraviolet photodetectors. Applied Physics Letters, 2012, 101, .	1.5	19
100	Optical polarization in c-plane Al-rich AlN/Al_xGa_{1-x}N single quantum wells. Applied Physics Letters, 2012, 101, 042103.	1.5	44
101	Band-edge transitions in hexagonal boron nitride epilayers. Applied Physics Letters, 2012, 101, 051110.	1.5	46
102	Epitaxial growth and demonstration of hexagonal BN/AlGaN p-n junctions for deep ultraviolet photonics. Applied Physics Letters, 2012, 100, .	1.5	93
103	Semiconducting hexagonal boron nitride for deep ultraviolet photonics. Proceedings of SPIE, 2012, , .	0.8	14
104	Origin of the significantly enhanced optical transitions in layered boron nitride. Physical Review B, 2012, 86, .	1.1	49
105	Dielectric strength, optical absorption, and deep ultraviolet detectors of hexagonal boron nitride epilayers. Applied Physics Letters, 2012, 101, .	1.5	118
106	Formation energy of optically active Er³⁺ centers in Er doped GaN. Applied Physics Letters, 2012, 101, 051114.	1.5	12
107	Threeâ€step growth method for high quality AlN epilayers. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 126-129.	0.8	24
108	Deep Ultraviolet Photoluminescence of Water-Soluble Self-Passivated Graphene Quantum Dots. ACS Nano, 2012, 6, 5102-5110.	7.3	1,526

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109	High-Quality Al-Rich AlGaN Alloys. Springer Series in Materials Science, 2012, , 29-81.	0.4	10
110	Current Injection Emitters at 1.54 Âµm Based on Erbium Doped GaN p-i-n Structures. , 2012, , .		0
111	Nitride MicroLEDs and Beyond - A Decade Progress Review. , 2012, , .		0
112	Photonic properties of erbium doped InGaN alloys grown on Si (001) substrates. Applied Physics Letters, 2011, 98, 081102.	1.5	13
113	Origin of background electron concentration in In <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>N alloys. Physical Review B, 2011, 84, .	1.1	40
114	Expanding into blue and green. Nature Photonics, 2011, 5, 521-522.	15.6	2
115	Impurities and conductivity control in Al-rich AlGaN alloys. , 2011, , .		0
116	Hexagonal boron nitride epitaxial layers as neutron detector materials. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2011, 654, 417-420.	0.7	105
117	Metastable Giant Moments in Gd-Implanted GaN, Si, and Sapphire. Journal of Superconductivity and Novel Magnetism, 2011, 24, 2123-2128.	0.8	4
118	Optical and magneto-optical properties of neodymium and erbium doped gallium nitride epilayers. , 2011, , .		0
119	III-Nitride full-scale high-resolution microdisplays. Applied Physics Letters, 2011, 99, .	1.5	270
120	Enhanced magnetization in erbium doped GaN thin films due to strain induced electric fields. Applied Physics Letters, 2011, 99, 122506.	1.5	12
121	Emission and absorption cross-sections of an Er:GaN waveguide prepared with metal organic chemical vapor deposition. Applied Physics Letters, 2011, 99, .	1.5	11
122	Epitaxially grown semiconducting hexagonal boron nitride as a deep ultraviolet photonic material. Applied Physics Letters, 2011, 98, .	1.5	178
123	Thermoelectric Properties of Er-doped InGaN Alloys for High Temperature Applications. Materials Research Society Symposia Proceedings, 2011, 1325, 41.	0.1	3
124	AlN. , 2011, , 21-68.		1
125	Achieving p-In x Ga1 -x N alloys with high In contents. , 2010, , .		0
126	III-nitride nanostructures for energy generation. , 2010, , .		0

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127	Evolution of phase separation in In-rich InGaN alloys. Applied Physics Letters, 2010, 96, .	1.5	40
128	Probing the relationship between structural and optical properties of Si-doped AlN. Applied Physics Letters, 2010, 96, 131906.	1.5	19
129	Nature of deep center emissions in GaN. Applied Physics Letters, 2010, 96, .	1.5	94
130	Carrier lifetime in erbium-doped GaN waveguide emitting in 1540 nm wavelength. Applied Physics Letters, 2010, 97, 241105.	1.5	17
131	1.54 Î¼m emitter and optical amplifier based on Er doped InGaN/GaN. , 2010, , .		1
132	Er-Doped GaN and InxGa1-xN for Optical Communications. Topics in Applied Physics, 2010, , 115-157.	0.4	6
133	InGaN/GaN multiple quantum well concentrator solar cells. Applied Physics Letters, 2010, 97, .	1.5	179
134	Hydrogen generation by solar water splitting using p-InGaN photoelectrochemical cells. Applied Physics Letters, 2010, 96, .	1.5	123
135	Enhancing erbium emission by strain engineering in GaN heteroepitaxial layers. Applied Physics Letters, 2010, 96, .	1.5	25
136	1.54 â€, Î¼ m emitters based on erbium doped InGaN p-i-n junctions. Applied Physics Letters, 2010, 97, .	1.5	43
137	Temperature-dependent photoluminescence and electron field emission properties of AlN nanotip arrays. Applied Physics Letters, 2009, 94, .	1.5	30
138	Electrical and optical properties of p-type InGaN. Applied Physics Letters, 2009, 95, .	1.5	66
139	High quality AlN for deep UV photodetectors. Applied Physics Letters, 2009, 95, .	1.5	44
140	The origin of 2.78 eV emission and yellow coloration in bulk AlN substrates. Applied Physics Letters, 2009, 95, .	1.5	51
141	Erbium-doped GaN optical amplifiers operating at 1.54â€,Î¼m. Applied Physics Letters, 2009, 95, 111109.	1.5	45
142	Deep ultraviolet photoluminescence of Tm-doped AlGaN alloys. Applied Physics Letters, 2009, 94, 111103.	1.5	8
143	Probing exciton-phonon interaction in AlN epilayers by photoluminescence. Applied Physics Letters, 2009, 95, .	1.5	23
144	Thermoelectric Properties of In0.3Ga0.7N Alloys. Journal of Electronic Materials, 2009, 38, 1132-1135.	1.0	30

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145	Optical enhancement of room temperature ferromagnetism in Er-doped GaN epilayers. Applied Physics Letters, 2009, 95, 022510.	1.5	22
146	Photoluminescence studies of impurity transitions in Mg-doped AlGaN alloys. Applied Physics Letters, 2009, 94, .	1.5	150
147	Photoluminescence properties of erbium doped InGaN epilayers. Applied Physics Letters, 2009, 95, 041113.	1.5	5
148	InGaN/GaN multiple quantum well solar cells with long operating wavelengths. Applied Physics Letters, 2009, 94, .	1.5	321
149	Spectroscopic studies of Er-centers in MOCVD grown GaN layers highly doped with Er. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 146, 193-195.	1.7	14
150	AlN MSM and Schottky photodetectors. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2148-2151.	0.8	13
151	Growth and optical properties of a-plane AlN and Al rich AlN/AlxGa1â€“xN quantum wells grown on r-plane sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1568-1570.	0.8	1
152	Thermoelectric properties of InxGa1â^'xN alloys. Applied Physics Letters, 2008, 92, .	1.5	105
153	Single phase InxGa1â^'xNâ€^(0.25â‰xâ‰0.63) alloys synthesized by metal organic chemical vapor deposition. Applied Physics Letters, 2008, 93, .	1.5	56
154	High mobility InN epilayers grown on AlN epilayer templates. Applied Physics Letters, 2008, 92, .	1.5	37
155	Structure and Photoluminescence Study of TiO₂ Nanoneedle Texture along Vertically Aligned Carbon Nanofiber Arrays. Journal of Physical Chemistry C, 2008, 112, 17127-17132.	1.5	135
156	Si-doped high Al-content AlGaN epilayers with improved quality and conductivity using indium as a surfactant. Applied Physics Letters, 2008, 92, .	1.5	36
157	III-nitride micro-emitter arrays: development and applications. Journal Physics D: Applied Physics, 2008, 41, 094001.	1.3	107
158	Direct hydrogen gas generation by using InGaN epilayers as working electrodes. Applied Physics Letters, 2008, 93, .	1.5	85
159	Characterization of AlN metal-semiconductor-metal diodes in the spectral range of 44â€“360nm: Photoemission assessments. Applied Physics Letters, 2008, 92, .	1.5	53
160	Valence band structure of AlN probed by photoluminescence. Applied Physics Letters, 2008, 92, 041114.	1.5	9
161	Beryllium acceptor binding energy in AlN. Applied Physics Letters, 2008, 93, .	1.5	15
162	Photoluminescence properties of AlN homoepilayers with different orientations. Applied Physics Letters, 2008, 93, .	1.5	28

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163	Current-injected 1.54Î¼m light emitting diodes based on erbium-doped GaN. Applied Physics Letters, 2008, 93, 033502.	1.5	23
164	Optical and magnetic behavior of erbium-doped GaN epilayers grown by metal-organic chemical vapor deposition. Applied Physics Letters, 2007, 91, .	1.5	28
165	Growth and photoluminescence studies of a-plane AlNâˆ•AlxGa1âˆ’xN quantum wells. Applied Physics Letters, 2007, 90, 221105.	1.5	19
166	Correlation between biaxial stress and free exciton transition in AlN epilayers. Applied Physics Letters, 2007, 91, 121117.	1.5	35
167	Correlation between optoelectronic and structural properties and epilayer thickness of AlN. Applied Physics Letters, 2007, 90, 241101.	1.5	123
168	Ultraviolet photoluminescence from ferromagnetic Fe-doped AlN nanorods. Applied Physics Letters, 2007, 90, 193118.	1.5	41
169	AlN avalanche photodetectors. Applied Physics Letters, 2007, 91, .	1.5	44
170	Mg acceptor level in InN epilayers probed by photoluminescence. Applied Physics Letters, 2007, 91, .	1.5	26
171	Hybrid AlNâ€“SiC deep ultraviolet Schottky barrier photodetectors. Applied Physics Letters, 2007, 90, 263505.	1.5	45
172	Achieving conductive high Al-content AlGaN alloys for deep UV photonics. , 2007, 6479, 265.		6
173	Effects of the wave function localization in AlInGaN quaternary alloys. Applied Physics Letters, 2007, 91, 061125.	1.5	38
174	Excitation dynamics of the 1.54Î¼m emission in Er doped GaN synthesized by metal organic chemical vapor deposition. Applied Physics Letters, 2007, 90, 051110.	1.5	41
175	Surface chemical and electronic properties of plasmaâ€treated nâ€type Al_{0.5}Ga_{0.5}N. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 3410-3416.	0.8	20
176	Ultraviolet photoluminescence from Gd-implanted AlN epilayers. Applied Physics Letters, 2006, 89, 152107.	1.5	45
177	Erbium-doped GaN epilayers synthesized by metal-organic chemical vapor deposition. Applied Physics Letters, 2006, 89, 151903.	1.5	57
178	III-Nitride Wide Bandgap Semiconductors for Optical Communications. , 2006, , .		0
179	Correlation between optical and electrical properties of Mg-doped AlN epilayers. Applied Physics Letters, 2006, 89, 152120.	1.5	113
180	AlGaNâˆ•GaNâˆ•AlN quantum-well field-effect transistors with highly resistive AlN epilayers. Applied Physics Letters, 2006, 88, 073513.	1.5	32

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181	Determination of energy-band offsets between GaN and AlN using excitonic luminescence transition in AlGaN alloys. Journal of Applied Physics, 2006, 99, 013705.	1.1	33
182	Effects of plasma treatment on the Ohmic characteristics of Tiâˆ•Alâˆ•Tiâˆ•Au contacts to n-AlGaN. Applied Physics Letters, 2006, 89, 082109.	1.5	46
183	Growth of III-nitride photonic structures on large area silicon substrates. Applied Physics Letters, 2006, 88, 171909.	1.5	72
184	Higher lying conduction band in GaN and AlN probed by photoluminescence spectroscopy. Applied Physics Letters, 2006, 88, 261919.	1.5	8
185	Exciton localization in AlGaN alloys. Applied Physics Letters, 2006, 88, 062103.	1.5	60
186	Thermally stable Schottky contacts on n-type GaN using ZrB2. Applied Physics Letters, 2006, 88, 183505.	1.5	20
187	III-nitride deep ultraviolet micro- and nano-photonics. , 2006, , .		1
188	Sublimation growth of aluminum nitride crystals. Journal of Crystal Growth, 2006, 297, 105-110.	0.7	18
189	GaN Light-Emitting Triodes for High-Efficiency Hole Injection. Journal of the Electrochemical Society, 2006, 153, G734.	1.3	2
190	Al rich AlN/AlGaN Quantum Wells. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
191	Erbium-doped GaN epilayers synthesized by metal-organic chemical vapor deposition. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
192	Time-resolved photoluminescence studies of Mg-doped AlN epilayers. , 2006, , .		0
193	Photoluminescence from Gd-implanted AlN and GaN Epilayers. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	1
194	Photoluminescence studies of impurity transitions in AlGaN alloys. Applied Physics Letters, 2006, 89, 092107.	1.5	119
195	Deep ultraviolet photoluminescence studies of AlN photonic crystals. Applied Physics Letters, 2006, 88, 133113.	1.5	10
196	Growth and photoluminescence studies of Zn-doped AlN epilayers. Applied Physics Letters, 2006, 89, 192111.	1.5	33
197	Growth and photoluminescence studies of Al-rich AlNâˆ•AlxGa1â^'xN quantum wells. Applied Physics Letters, 2006, 89, 131922.	1.5	31
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